

MICROELECTRONICS

AN INTEGRATED APPROACH

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Prentice Hall Electronic and VLSI Series
Charles G. Sodini, Series Editor



Prentice Hall, Upper Saddle River, New Jersey 07458



Library of Congress Cataloging-in-Publication Data

Howe, Roger Thomas.

Microelectronics : an integrated approach / Roger T. Howe,
Charles G. Sodini.

p. cm.

Includes bibliographical references and index.

ISBN 0-13-588518-3

1. Microelectronics. 2. Solid state electronics. I. Sodini,
Charles G. II. Title.
TK7874.H688 1997
621.3815--dc20

96-17867
CIP

Acquisitions editor: Eric Svendsen

Production service: TKM Productions

Editorial/production supervision: Sharyn Vitrano

Copy editor: TKM Productions

Interior design: Lisa Delgado

Cover design: Joseph Sengotta

Art director: Amy Rosen

Managing editor: Bayani Mendoza DeLeon

Editor-in-chief: Marcia Horton

Director of production and manufacturing: David W. Riccardi

Manufacturing buyer: Julia Meehan

Editorial assistant: Kathryn Cassino



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Simon & Schuster / A Viacom Company
Upper Saddle River, New Jersey 07458

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mance, or use of these programs.

Printed in the United States of America

10 9 8 7 6 5

ISBN 0-13-588518-3

Prentice-Hall International (UK) Limited, London
Prentice-Hall of Australia Pty. Limited, Sydney
Prentice-Hall Canada Inc., Toronto
Prentice-Hall Hispanoamericana, S.A., Mexico
Prentice-Hall of India Private Limited, New Delhi
Prentice-Hall of Japan, Inc., Tokyo
Simon & Schuster Asia Pte. Ltd., Singapore
Editora Prentice-Hall do Brasil, Ltda., Rio de Janeiro

To our families,

Jenny

Nathan, Julie, Debbie and Greg

R. T. H.

Anne

Maria and John

C. G. S.

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